CVD Equipment 1033
Tube 1 - OXIDE

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Process Summary
Thermal oxidation of silicon in dry oxygen or pyrogenic steam. Maximum allowed temperature is 1100 °C.

Process Preparation
All samples must be RCA cleaned (SC1 and SC2) before being placed in the CVD Equipment 1033 furnace. 4” whole wafers preferred, smaller sizes can be accommodated.

<table>
<thead>
<tr>
<th>Only these Materials are Allowed</th>
<th>Known Forbidden Materials</th>
</tr>
</thead>
<tbody>
<tr>
<td>Silicon</td>
<td>☓ Metal</td>
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</table>

For any material not listed or if uncertain, **ASK** the Tool Owner!